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 - The abstract of the paper
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- Equations should be
 - written using Microsoft or MathType Equation Editor;
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- References should be:
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References (examples):

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Journal articles

- [1] Shunin Yu N, Zhukovskii Yu F, Gopejenko V I, Burlutskaya N, Lobanova-Shunina T, Bellucci S 2012 *Journal of Nanophotonics* **6**(1) 31-6

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- [6] Dorman L I 1975 *Variations of Galactic Cosmic Rays* Moscow State University Press: Moscow p 103
- [7] Caplar R and Kulisic P 1973 *Proc. Int. Conf. on Nuclear Physics (Munich)* **1** North-Holland/American Elsevier: Amsterdam p 517
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Internet recourses

- [14] Ram R, Orlando T 2003 *Physics for Solid-State Applications* <http://ocw.mit.edu/courses/electrical-engineering-and-computer-science/6-730-physics-for-solid-state-applications-spring-2003/> 16 Jan 2014

Work written in a nonLatin script

- [15] Grosberg A. Yu. and Khokhlov A. R., 1989 *Statistical Physics of Macromolecules* Nauka: Moscow (in Russian)
- [16] Kireev S V, Protsenko E D, Shyrev S L 2002 *Byull. Izobret.* No. 10 RF Patent No.2181197 (in Russian)

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2 Another section of the thesis/paper

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2.1 A SUBSECTION

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Figure

FIGURE 1 Figure title

Figure

FIGURE 2 Figure title

Figure

FIGURE 3 Figure title

TABLE 1 Table title

Column title	Column title	Column title
Text	Text	Text
Text	Text	Text

$$\tilde{S}_\alpha(t, M) = \sum_{k=1}^M (\tilde{a}_k \sin(\tilde{x}_k t) X_k + \tilde{b}_k (1 - \cos(\tilde{y}_k t)) Y_k) \quad (1)$$

2.2.1 A subsubsection.

The first paragraph after a heading is not indented.

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3 Conclusions

Acknowledgements

Appendix A Appendix title

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- [4] Eaton D I 1975 *Porous glass support material* US Patent No. 3 904

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